

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Please cancel claims 7 through 12 without prejudice or disclaimer.

Please rewrite claims 1-3 and 5 as follows:

Listing of Claims:

Claim 1 (Currently Amended): A method for fabricating a III-V nitride film, comprising the steps of:

~~preparing~~ providing a horizontal reactor ~~horizontally~~[[,]];

setting a substrate onto a susceptor installed in the reactor[[,]];

heating the substrate to a predetermined temperature[[,]];

directly cooling at least [[the]] a portion of the inner wall of the reactor directly opposite to the substrate[[,]]; and

introducing a [[III]] raw III material gas and a [[V]] raw V material gas with a carrier gas onto the substrate, ~~and thus, fabricating to form~~ a III-V nitride film [[by]] using a MOCVD method.

Claim 2 (Currently Amended): A fabricating method as defined in claim 1, wherein the susceptor is set on the bottom wall of the reactor, and ~~the opposite~~ a portion of the top wall of the reactor opposite to the substrate set on the susceptor is cooled down.

Claim 3 (Currently Amended): A fabricating method as defined in claim 1, wherein [[the]] an upper stream side of the reactor ~~from with respect to~~ the substrate set on the susceptor is cooled down.

Claim 4 (Original): A fabricating method as defined in claim 1, wherein the whole of the reactor is cooled down.

Claim 5 (Currently Amended): A fabricating method as defined in claim 1, wherein the III-V nitride film is an Al-rich ~~Al_xGa_yIn_zN~~ Al_xGa_yIn_zN ($x+y+z=1$, $x>0.5$, $y\geq 0$, $z\geq 0$) film.

Claim 6 (Original): A fabricating method as defined in claim 1, wherein the III-V nitride film is an AlN film.

Claims 7-12 (Cancelled).